



# STP100NF04 STB100NF04, STB100NF04-1

N-CHANNEL 40V - 0.0043Ω - 120A TO-220/D<sup>2</sup>PAK/I<sup>2</sup>PAK  
STripFET™ II POWER MOSFET

AUTOMOTIVE SPECIFIC

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STP100NF04	40 V	< 0.0046 Ω	120 A	300 W
STB100NF04	40 V	< 0.0046 Ω	120 A	300 W
STB100NF04-1	40 V	< 0.0046 Ω	120 A	300 W

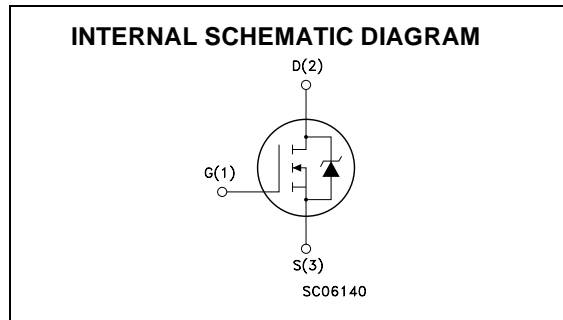
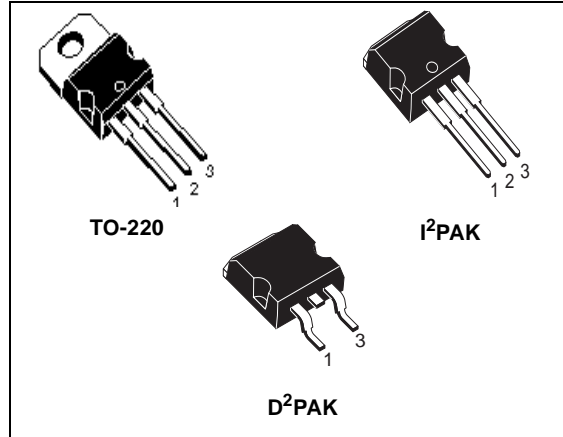
- TYPICAL R<sub>DS(on)</sub> = 0.0043 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED

## DESCRIPTION

This Power Mosfet is the latest development of ST-Microelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

## APPLICATIONS

- HIGH CURRENT, HIGH SWITCHING SPEED



## ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP100NF04	P100NF04	TO-220	TUBE
STB100NF04T4	B100NF04	D <sup>2</sup> PAK	TAPE & REEL
STB100NF04-1	B100NF04	I <sup>2</sup> PAK	TUBE

## STP100NF04, STB100NF04, STB100NF04-1

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	40	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	40	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub> (#)	Drain Current (continuous) at T <sub>C</sub> = 25°C	120	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	120	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	480	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	300	W
	Derating Factor	2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	6	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	1.2	J
T <sub>j</sub>	Operating Junction Temperature	-55 to 175	°C
T <sub>stg</sub>	Storage Temperature		

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 120A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25°C, I<sub>d</sub> = 60A, V<sub>DD</sub> = 30 V

(#) Current Limited by Package

### THERMAL DATA

		TO-220 / I <sup>2</sup> PAK / D <sup>2</sup> PAK	
R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	0.5	°C/W
R <sub>thj-pcb</sub>	Thermal Resistance Junction-pcb Max	See Curve on page 6	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient (Free air) Max	62.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	40			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50 A		0.0043	0.0046	Ω

## ELECTRICAL CHARACTERISTICS (CONTINUED)

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (1)	Forward Transconductance	$V_{DS} = 15\text{ V}$ , $I_D = 50\text{ A}$		150		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		5100 1300 160		pF pF pF

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 20\text{ V}$ , $I_D = 60\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		35 220		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 32\text{ V}$ , $I_D = 120\text{ A}$ , $V_{GS} = 10\text{ V}$ (see, Figure 4)		110 35 35	150	nC nC nC

## SWITCHING OFF

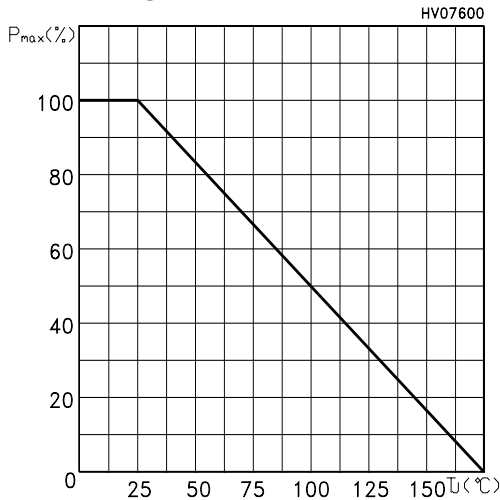
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 20\text{ V}$ , $I_D = 60\text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		80 50		ns ns

## SOURCE DRAIN DIODE

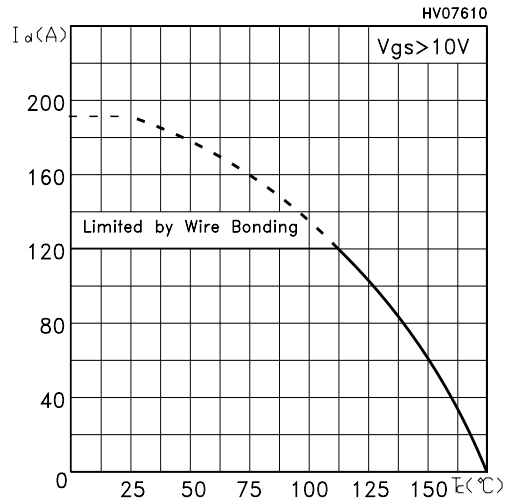
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$ (2)	Source-drain Current Source-drain Current (pulsed)				120 480	A A
$V_{SD}$ (1)	Forward On Voltage	$I_{SD} = 120\text{ A}$ , $V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 120\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ , $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		75 185 5		ns nC A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

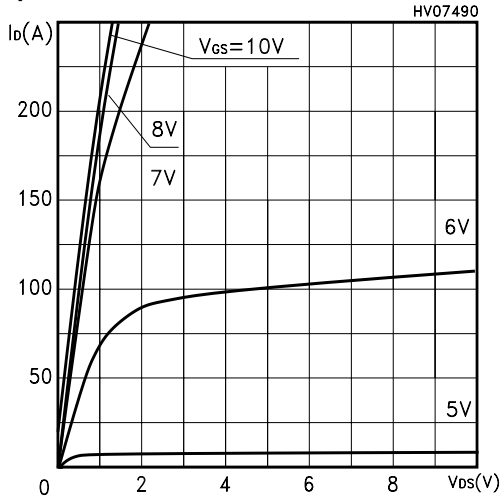
Power Derating vs Tc



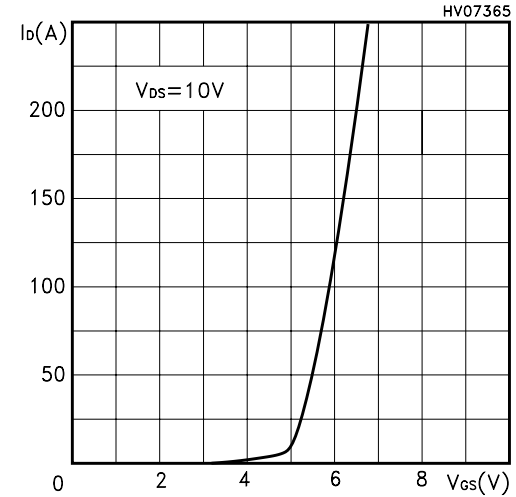
Max Id Current vs Tc



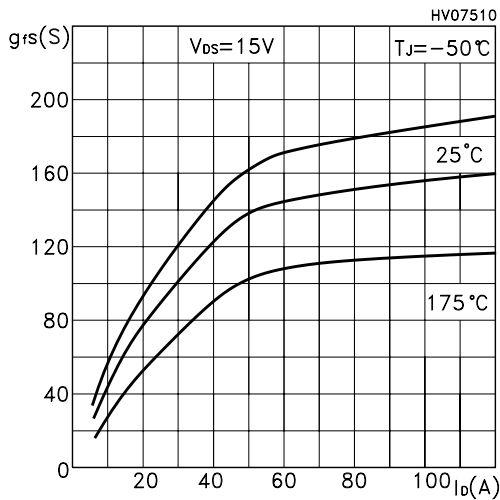
Output Characteristics



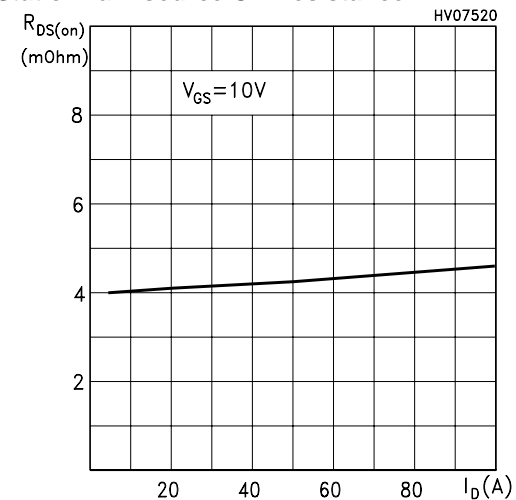
Transfer Characteristics



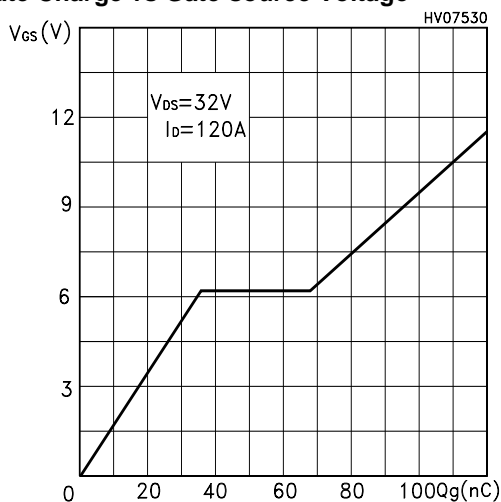
Transconductance



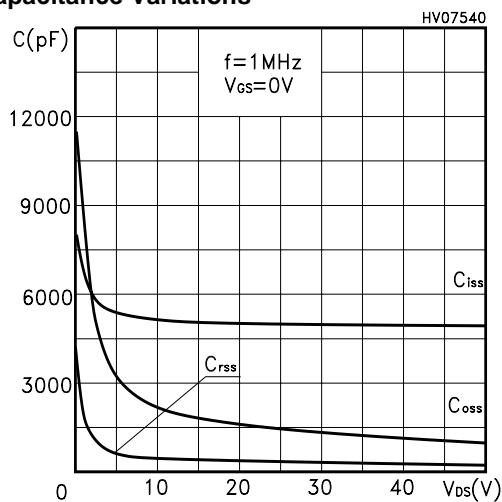
Static Drain-source On Resistance



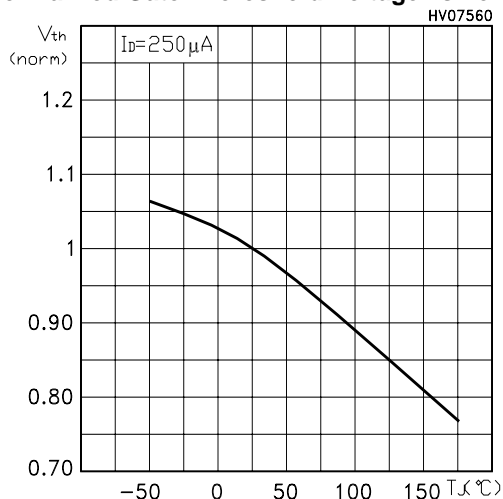
Gate Charge vs Gate-source Voltage



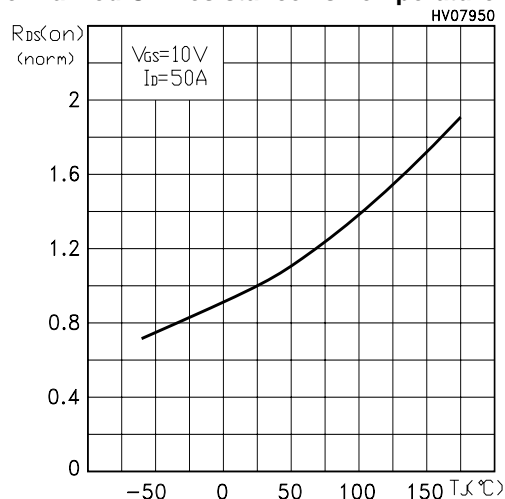
Capacitance Variations



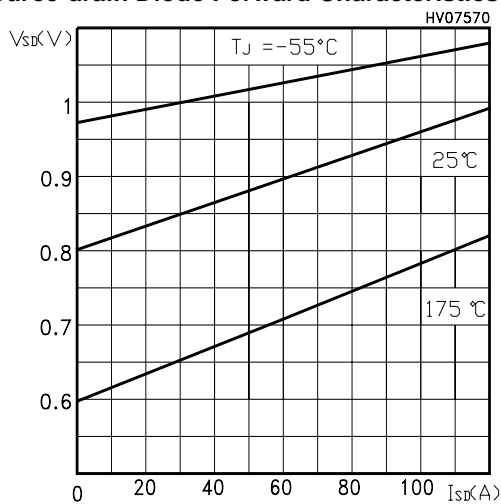
Normalized Gate Threshold Voltage vs Temp.



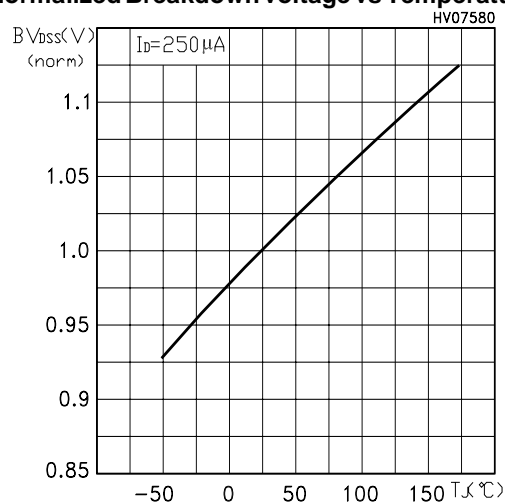
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

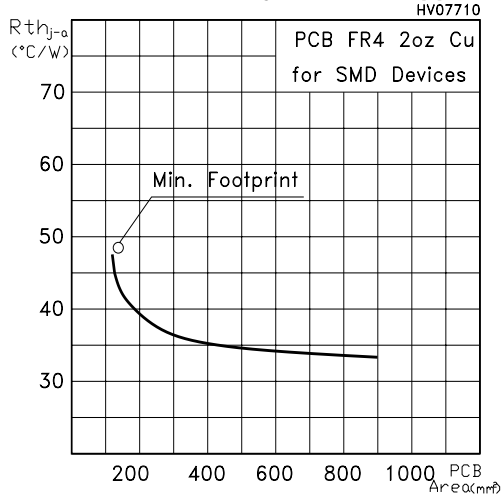


Normalized Breakdown voltage vs Temperature

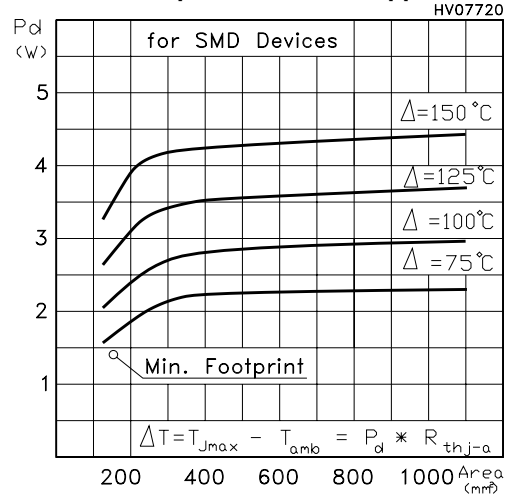


**STP100NF04, STB100NF04, STB100NF04-1**

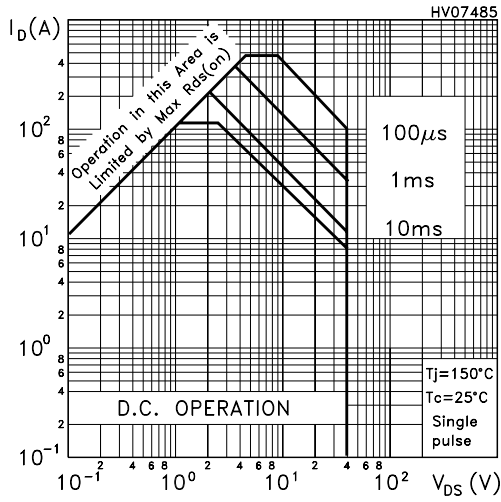
**Thermal Resistance Rthj-a vs PCB Copper Area**



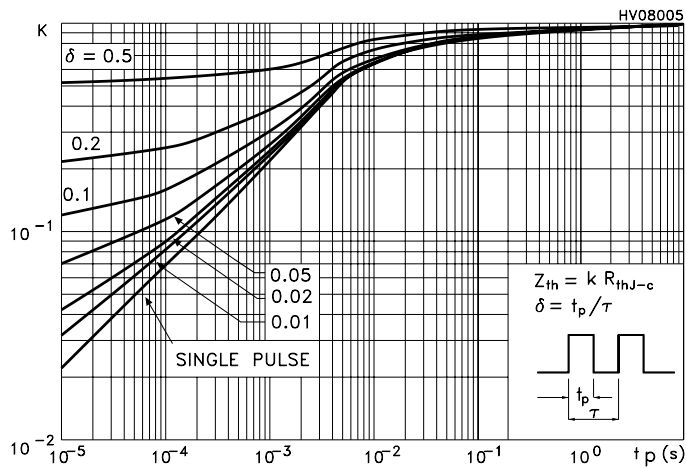
**Max Power Dissipation vs PCB Copper Area**



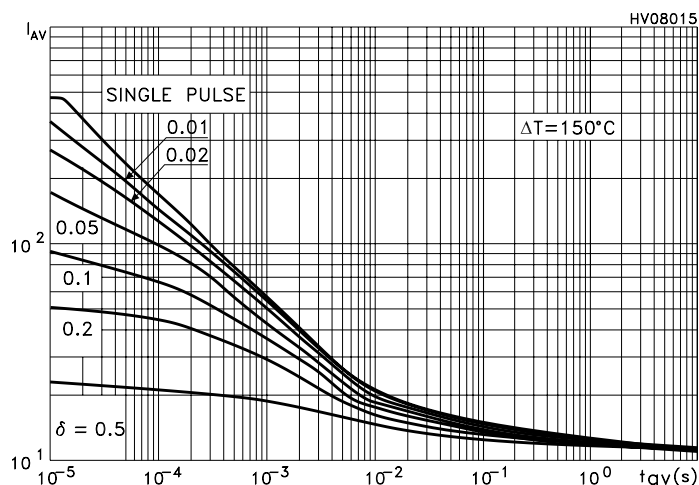
**Safe Operating Area**



**Thermal Impedance**



Allowable  $I_{AV}$  vs. Time in Avalanche



The previous curve gives the safe operating area for unclamped inductive loads, single pulse or repetitive, under the following conditions:

$$P_{D(AVE)} = 0.5 * (1.3 * BV_{DSS} * I_{AV})$$

$$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$$

Where:

$I_{AV}$  is the Allowable Current in Avalanche

$P_{D(AVE)}$  is the Average Power Dissipation in Avalanche (Single Pulse)

$t_{AV}$  is the Time in Avalanche

To derate above  $25^\circ\text{C}$ , at fixed  $I_{AV}$ , the following equation must be applied:

$$I_{AV} = 2 * (T_{jmax} - T_{CASE}) / (1.3 * BV_{DSS} * Z_{th})$$

Where:

$Z_{th} = K * R_{th}$  is the value coming from Normalized Thermal Response at fixed pulse width equal to  $T_{AV}$ .

**SPICE THERMAL MODEL**

Parameter	Node	Value
CTHERM1	5 - 4	0.011
CTHERM2	4 - 3	0.0012
CTHERM3	3 - 2	0.05
CTHERM4	2 - 1	0.1
RTHERM1	5 - 4	0.09
RTHERM2	4 - 3	0.02
RTHERM3	3 - 2	0.11
RTHERM4	2 - 1	0.17

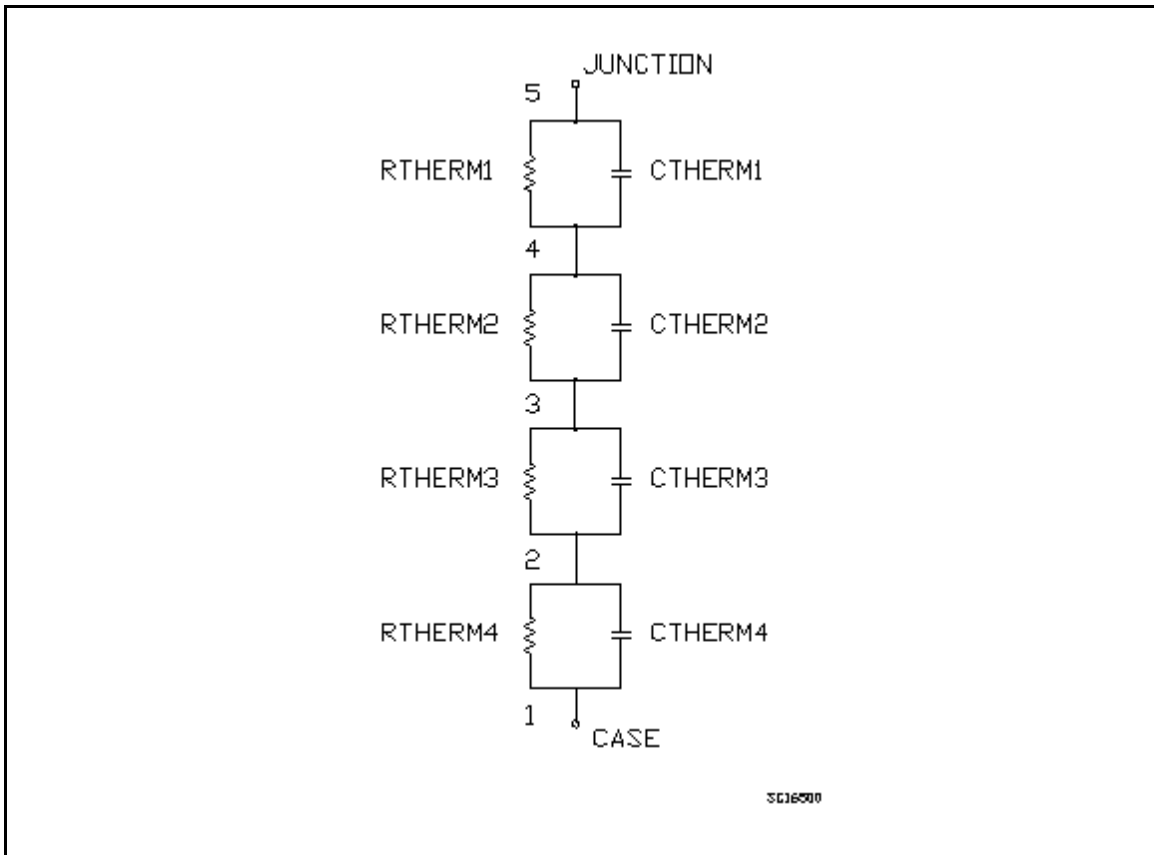




Fig. 1: Unclamped Inductive Load Test Circuit

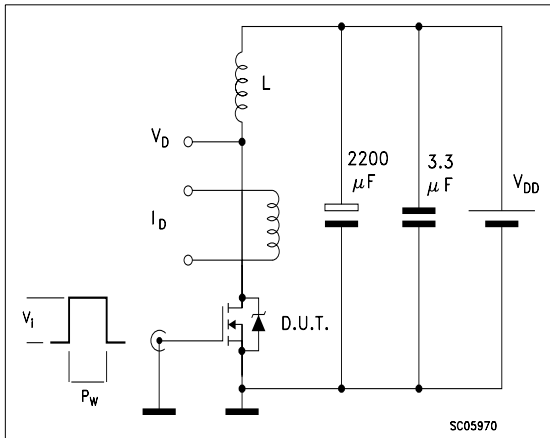


Fig. 2: Unclamped Inductive Waveform

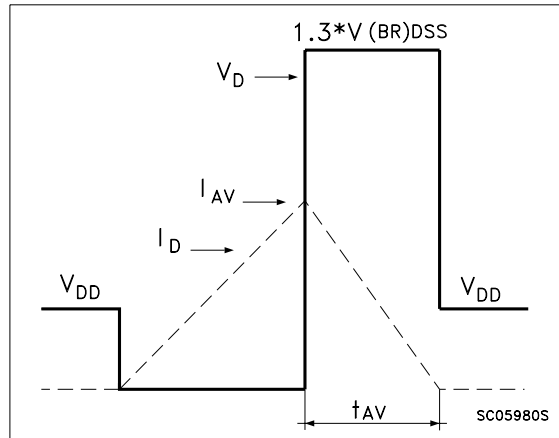


Fig. 3: Switching Times Test Circuit For Resistive Load

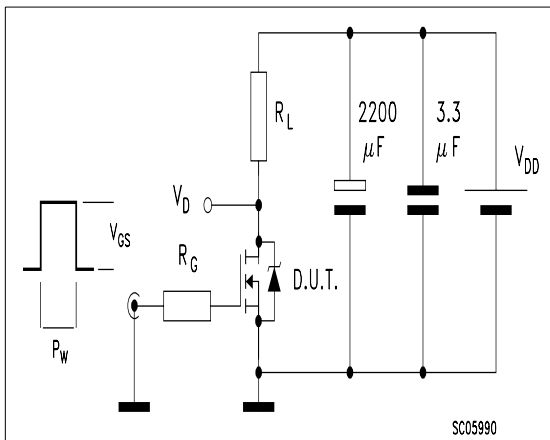


Fig. 3.1: Inductive Load Switching And Diode Recovery Times Waveform

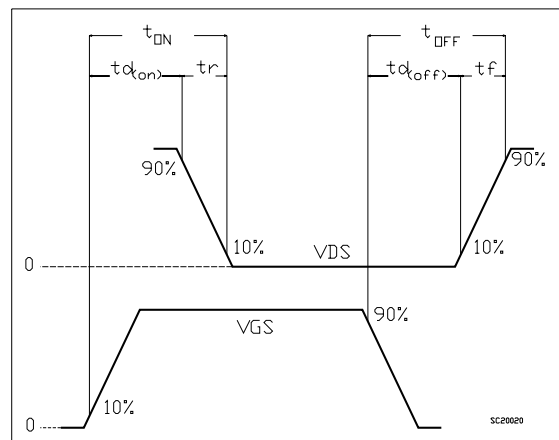


Fig. 4: Gate Charge test Circuit

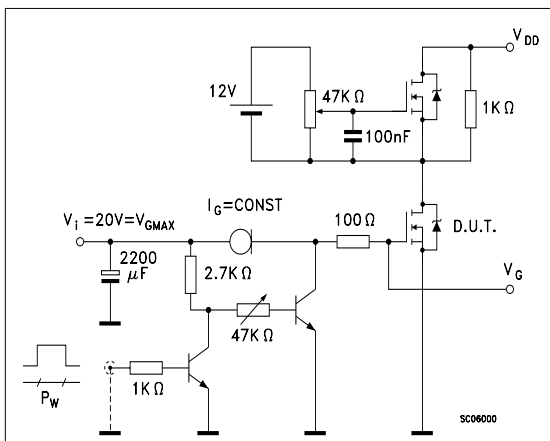


Fig. 4.1: Gate Charge test Waveform

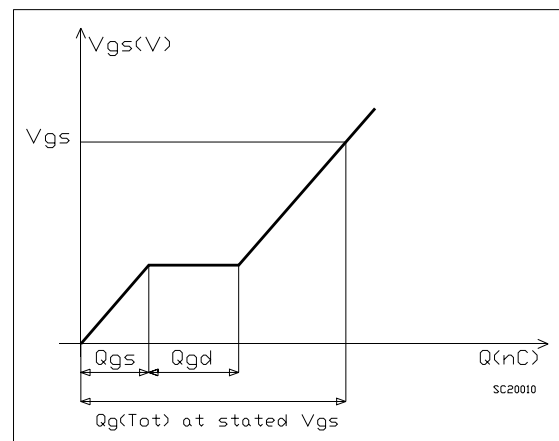


Fig. 5: Test Circuit For Diode Recovery Times

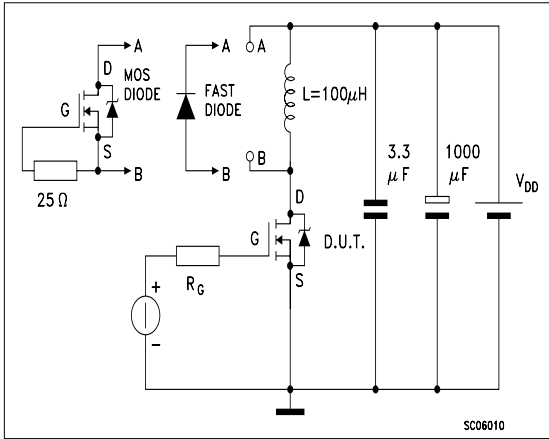
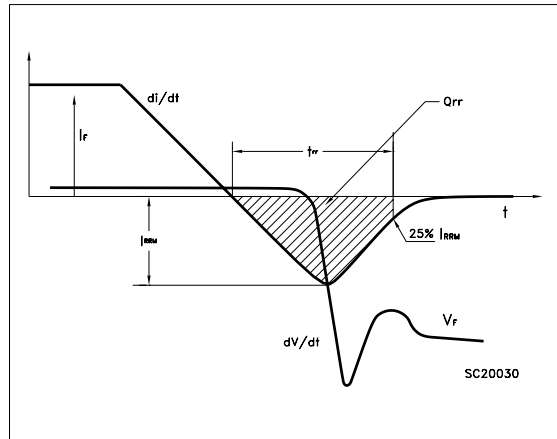
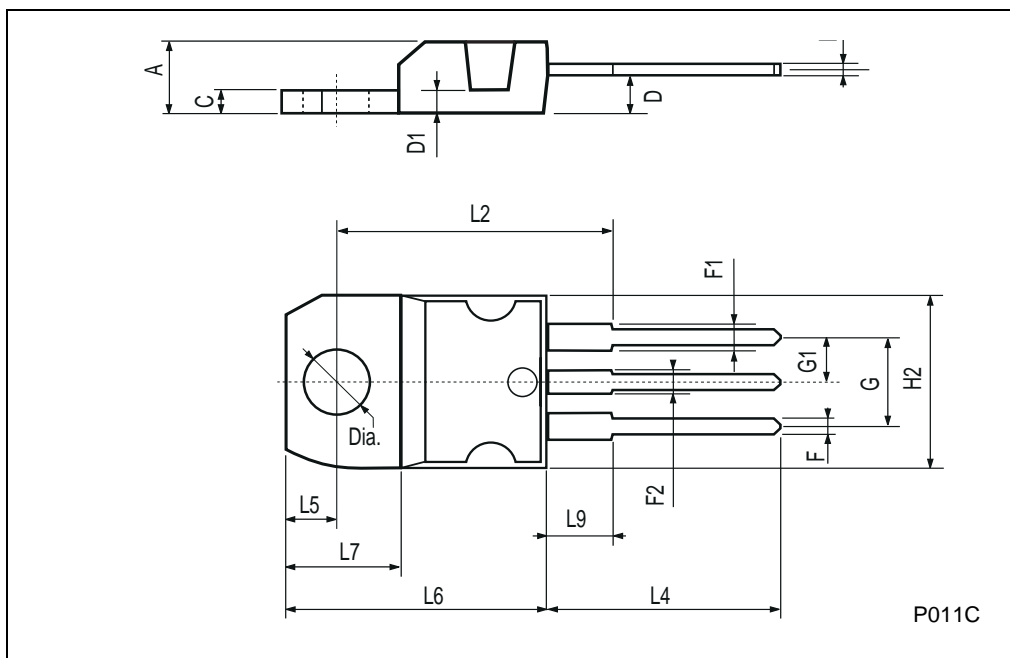


Fig. 5.1: Diode Recovery Times Waveform



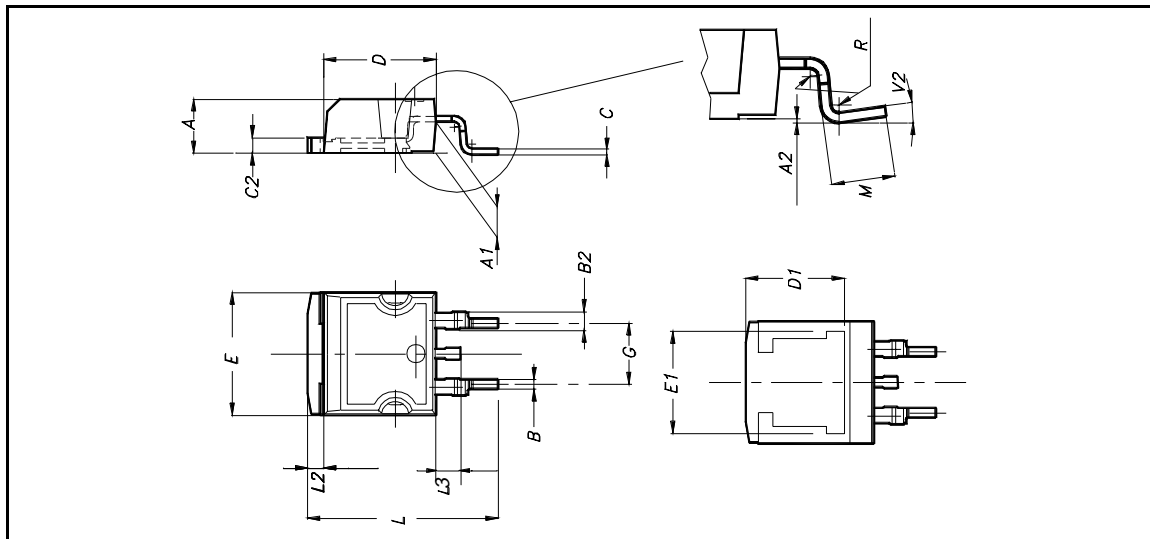
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



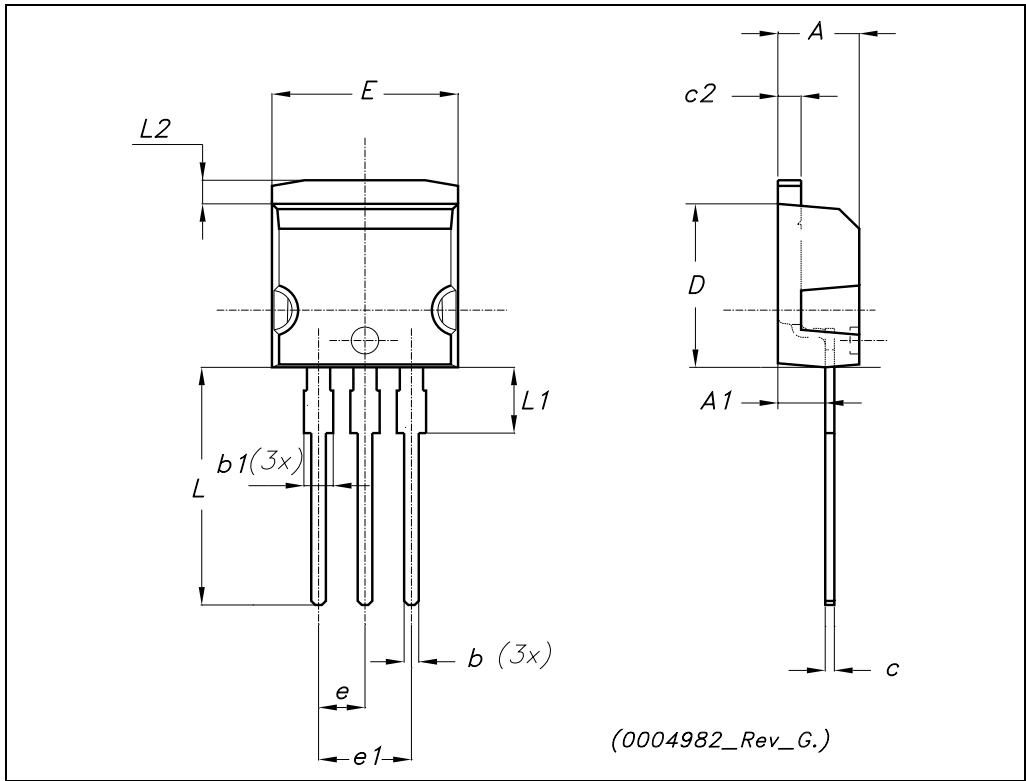
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			

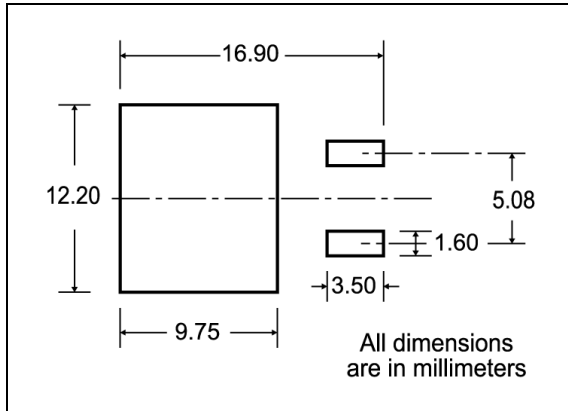


**TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA**

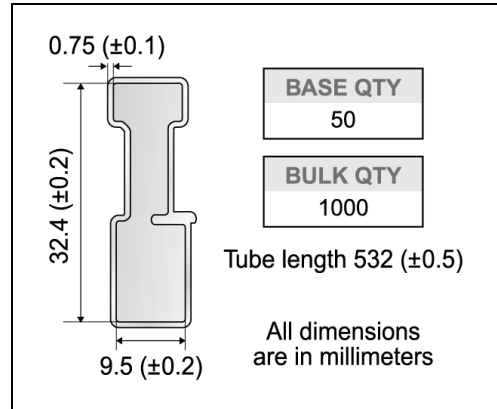
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



**D<sup>2</sup>PAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

\* on sales type  
14/15



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